

Silicon NPN Power Transistors

BUL742

DESCRIPTION

- With TO-220C package
- High voltage capability
- Very high switching speed

APPLICATIONS

Silicon NPN Power Transistors

BUL742

CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; L=25mH	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	12			
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =1A ; I _B =0.2A			0.5	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =2A ; I _B =0.4A			1.0	V
V _{CEsat-3}	Collector-emitter saturation voltage	I _C =4A ; I _B =0.8A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A ; I _B =0.4A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =900V; V _{BE} =0			100	μ A
h _{FE-1}	DC current gain	I _C =250mA ; V _{CE} =5V	35		70	
h _{FE-2}	DC current gain	I _C =2A ; V _{CE} =5V	10		35	

Switching times resistive load

t _s	Storage time	V _{CC} =125V , I _C =0.5A I _{B1} =-I _{B2} =45mA t _p =300μ s		11		μ s
t _f	Fall time			0.25		μ s

